

RoHS Compliant Product  
A suffix of "-C" specifies halogen & lead-free

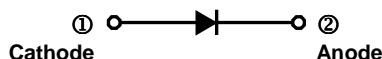
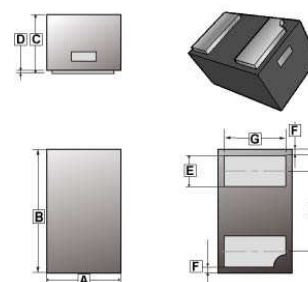
## DESCRIPTION

- Silicon epitaxial planar Schottky barrier Diodes
- Small surface mounting type
- High reliability
- Low reverse current and low forward voltage

## APPLICATION

- High speed switching For Detection
- For portable equipment:  
(i.e. Mobile phone, MP3, MD, CD-ROM,  
DVD-ROM, Note book PC, etc.)

### DFNWB



## PACKAGE INFORMATION

Weight: 0.0123 g (approximately)

REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	0.55	0.65	E	0.15	0.35
B	0.95	1.05	F	0.05REF	
C	0.4	0.5	G	0.4	0.6
D	0	0.05	H	0.65TYP	

## MARKING CODE

Cathode - •E +Anode

## MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS (Single diode at $T_A = 25^\circ\text{C}$ )

Parameter	Symbol	Limits	Unit
DC Reverse Voltage	$V_R$	30	V
Mean Rectifying Current	$I_O$	100	mA
Peak Forward Surge Current	$I_{FSM}$	500	mA
Junction, Storage Temperature	$T_J, T_{STG}$	+125, -40 ~ +125	$^\circ\text{C}$

## ELECTRICAL CHARACTERISTICS (at $T_A = 25^\circ\text{C}$ unless otherwise specified)

Parameters	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Forward Voltage	$V_F$	-	-	0.45	V	$I_F = 10\text{mA}$
Reverse Current	$I_R$	-	-	0.5	$\mu\text{A}$	$V_R = 10\text{V}$

**RATINGS AND CHARACTERISTIC CURVES**

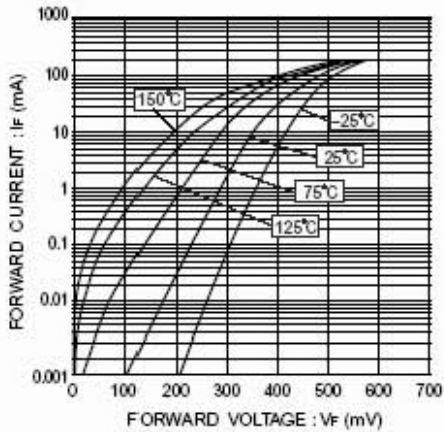


Fig.1 Forward characteristics

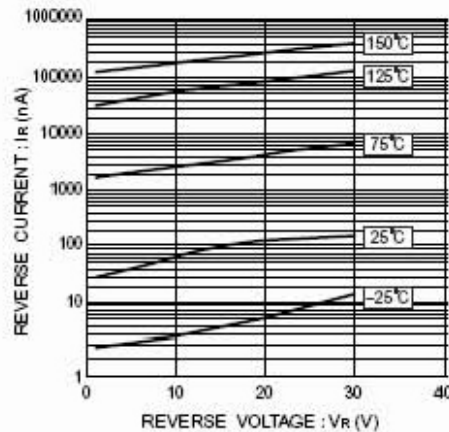


Fig.2 Reverse characteristics

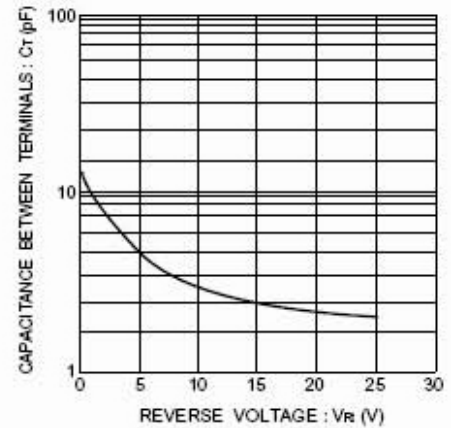


Fig. 3 Capacitance between terminals characteristics